

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

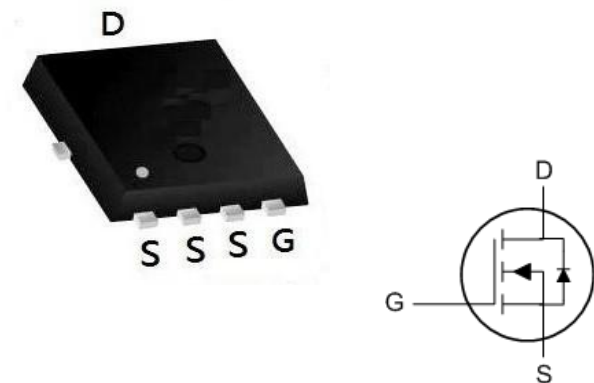


BVDSS	RDSON	ID
40V	4.6mΩ	80A

Description

The RST80N04F is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and gate charge for most of the synchronous buck converter applications. The RST80N04F meets the RoHS and Green Product requirements, 100% EAS guaranteed with full function reliability approved.

PDFN5060-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	52	A
I_{DM}	Pulsed Drain Current ²	320	A
EAS	Single Pulse Avalanche Energy ³	104	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	77	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	---	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.95	$^\circ C/W$

Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	---	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=1A$	---	4.6	5.9	m Ω
		$V_{GS}=4.5V$, $I_D=1A$	---	5.7	7.2	
		$V_{GS}=2.5V$, $I_D=1$	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	0.85	1.35	1.95	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/ $^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=40V$, $V_{GS}=0V$, $T_J=125^{\circ}\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=20A$	---	---	---	S
Q_g	Total Gate Charge	$V_{DS}=20V$, $V_{GS}=10V$, $I_D=30A$	---	57	---	nC
Q_{gs}	Gate-Source Charge		---	9	---	
Q_{gd}	Gate-Drain Charge		---	11	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=20V$, $V_{GS}=10V$, $R_G=3\Omega$	---	8	---	ns
T_r	Rise Time		---	18	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24	---	
T_f	Fall Time		---	14	---	
C_{iss}	Input Capacitance	$V_{DS}=20V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3042	---	pF
C_{oss}	Output Capacitance		---	386	---	
C_{rss}	Reverse Transfer Capacitance		---	232	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	80	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=20A$, $di/dt=100A/\mu s$, $T_J=25^{\circ}\text{C}$	---	22	---	nS
Q_{rr}	Reverse Recovery Charge		---	11	---	nC

Note :

- 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2.EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=40V$, $V_G=10V$, $R_G=25\Omega$, $L=0.5\text{mH}$.
- 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Performance

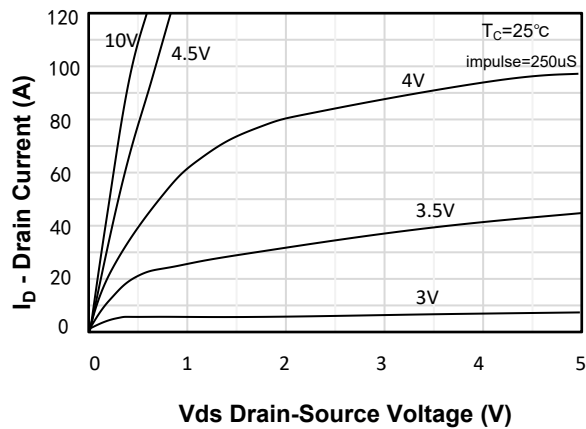


Figure 1. On-Region Characteristics

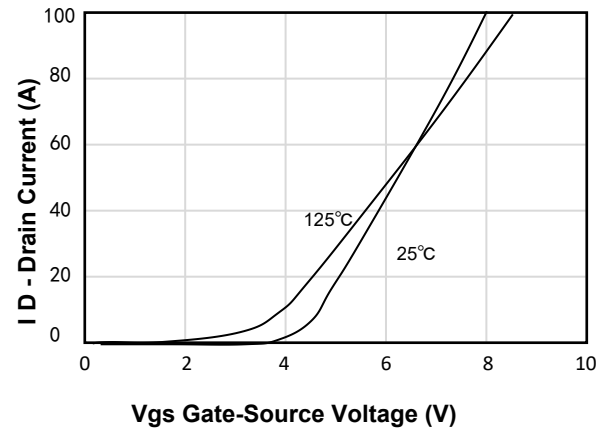


Figure 2. Transfer Characteristics

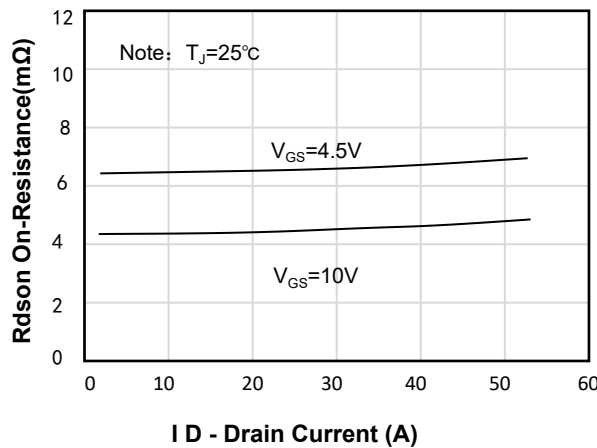


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

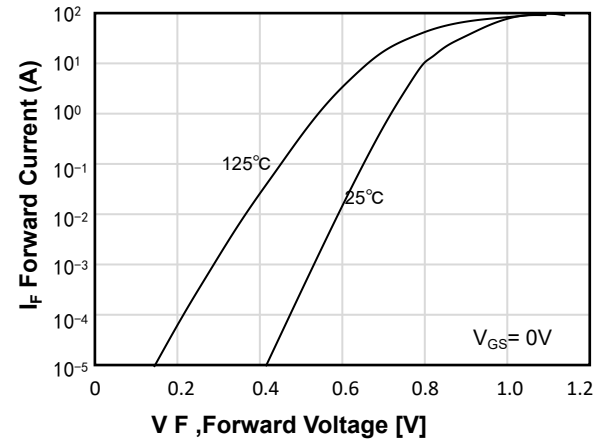


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

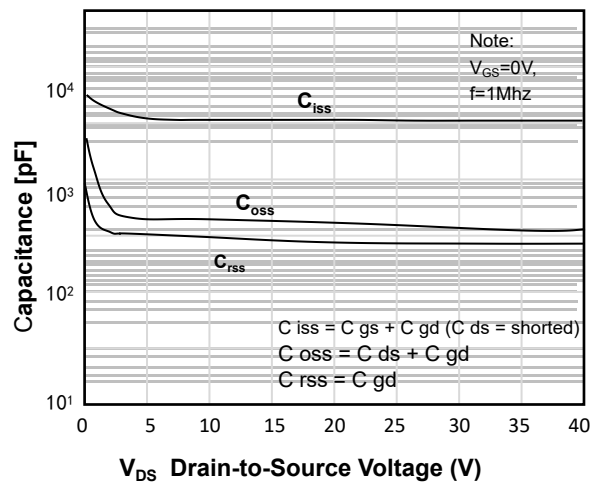


Figure 5. Capacitance Characteristics

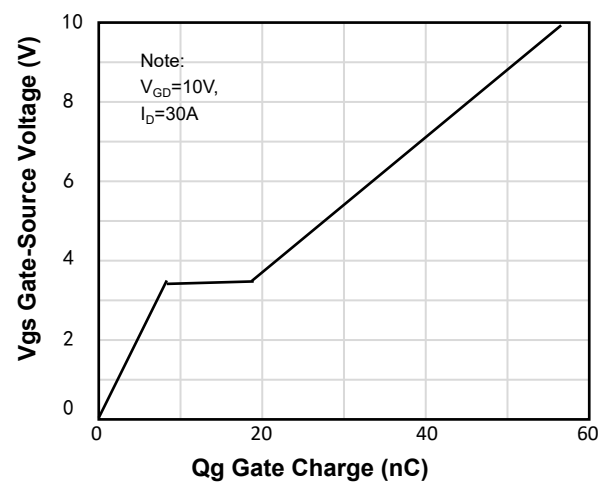


Figure 6. Gate Charge Characteristics

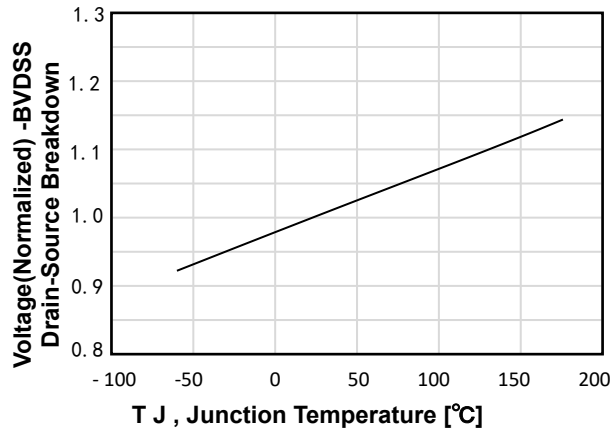


Figure 7. Breakdown Voltage Variation vs Temperature

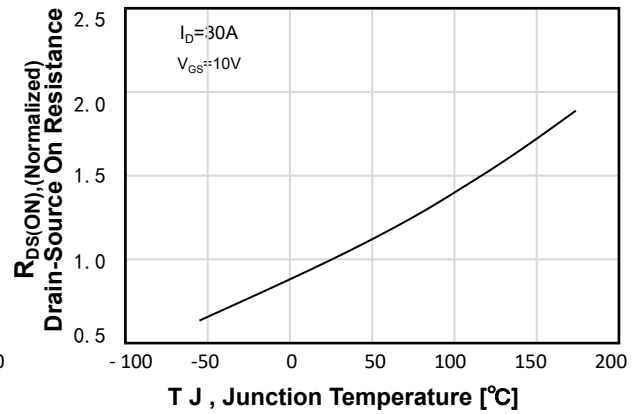


Figure 8. On-Resistance Variation vs Temperature

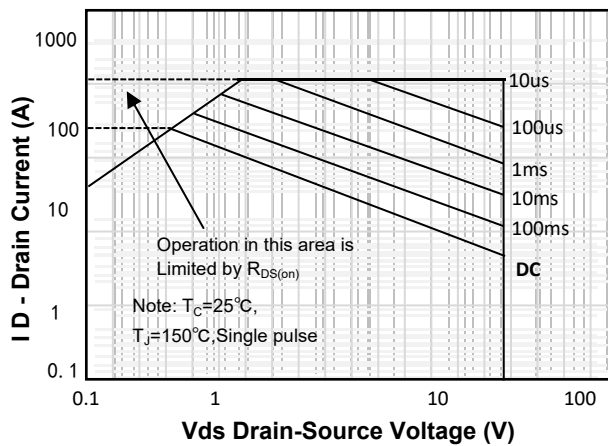


Figure 9. Maximum Safe Operating Area

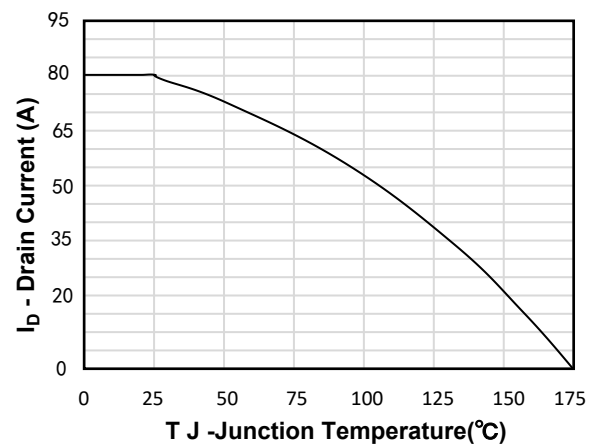


Figure 10. Vds Drain VS Junction Temperature

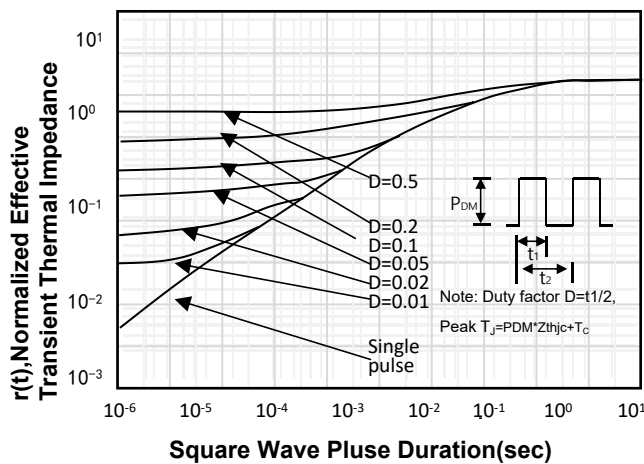


Figure 11. Transient Thermal Response Curve

Test Circuit

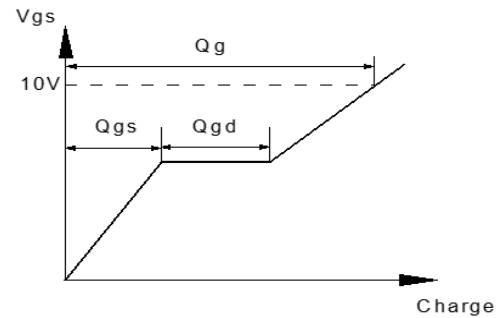
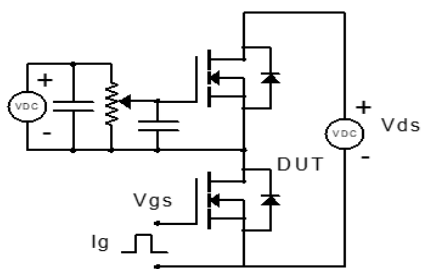


Figure 1: Gate Charge Test Circuit & Waveform

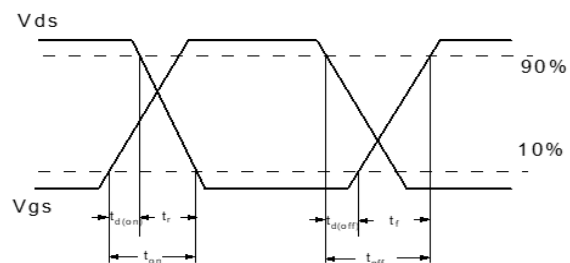
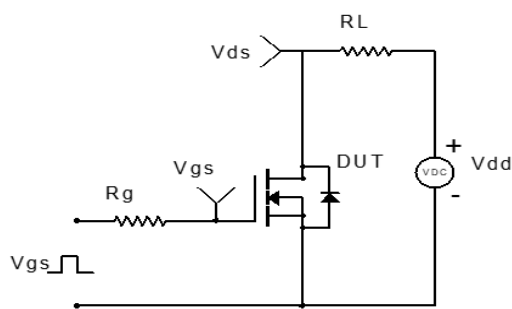


Figure 2: Resistive Switching Test Circuit & Waveform

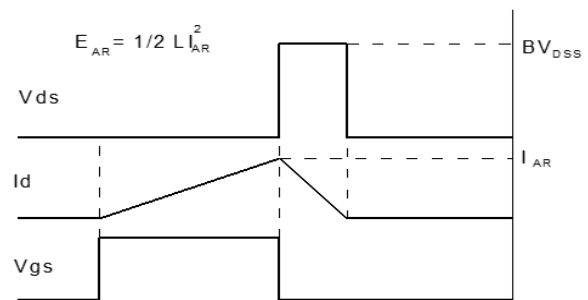
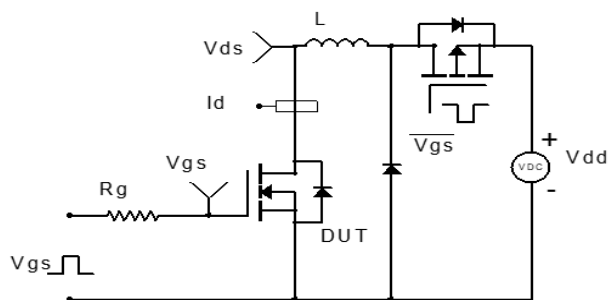


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

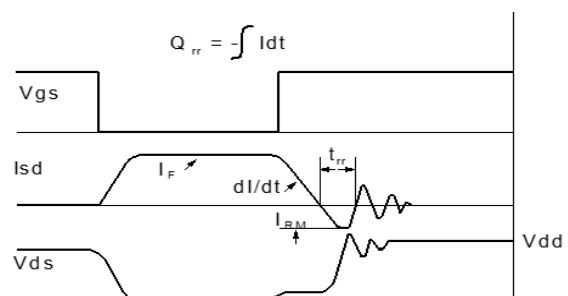
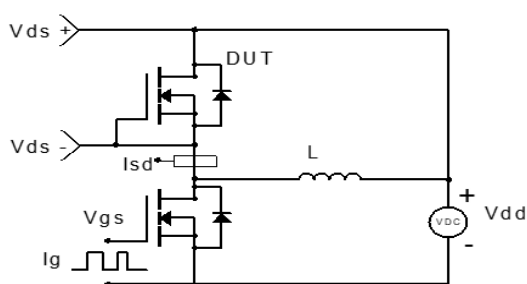
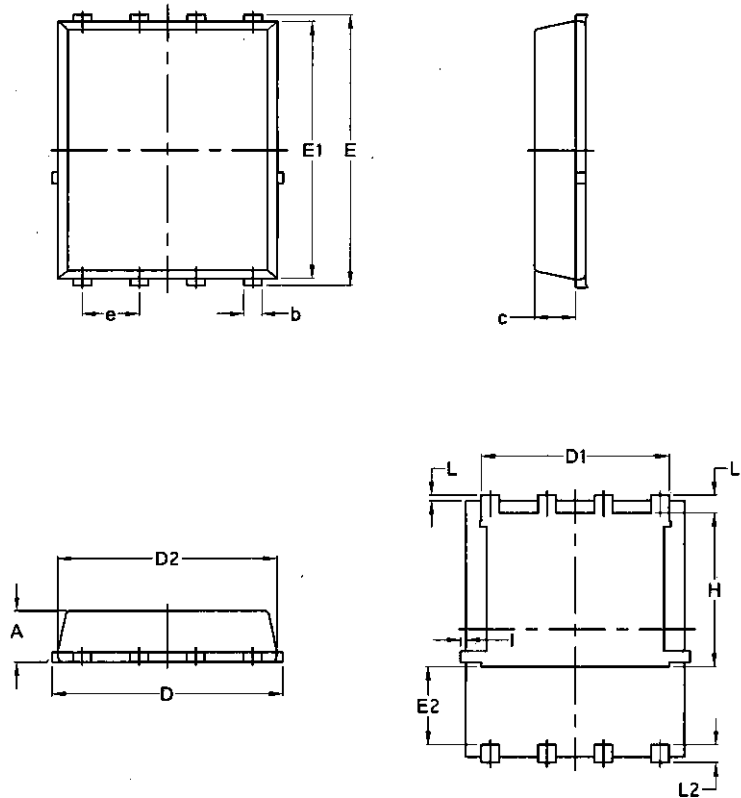


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data-PDFN5060-8L-Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070